

FEATURES

- High Speed Switching
- High Blocking Voltage with Low $R_{DS(on)}$
- Easy to Parallel
- Simple to Drive
- RoHS Compliant

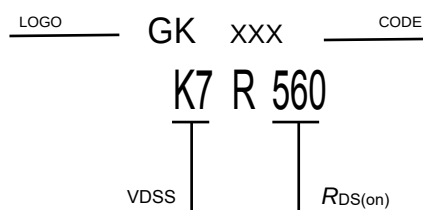
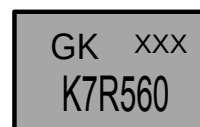
APPLICATION

- Increased Power Density
- Faster Operating Frequency
- Reduction of Heat Sink Requirements
- Higher Efficiency
- Reduced EMI

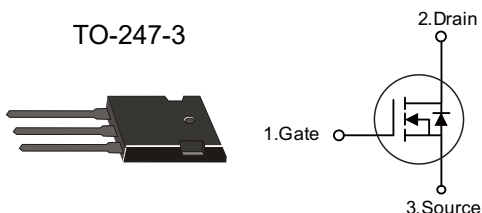
APPLICATION

- Power Factor Correction Modules
- Switch Mode Power Supplies
- DC-AC Inverters
- High Voltage DC/DC Converters

V_{DS} 1700V
 I_D 9 A
 $R_{DS(ON)}$ 565 m Ω



TO-247-3



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit
V_{DS}	Drain-Source Voltage		1700	V
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$	9 6	A
I_{DM}	Peak Drain Current	Pulse width t_p limited by T_{jmax}	16	A
V_{GSmax}	Gate-Source Voltage		-8/+22	V
V_{GSop}	Recommend Gate-Source Voltage		-4/+18	V
P_{tot}	Power Dissipation	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$	98 49	W
T_j	Operating Junction Temperature		-40~175	$^\circ\text{C}$
T_{stg}	Storage Temperature		-40~175	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D=100\mu\text{A}$, $V_{GS}=0\text{V}$	1700			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=1700\text{V}$, $V_{GS}=0\text{V}$		1		μA
I_{GSS}	Gate-Source Leakage Current	$V_{DS}=0\text{V}$, $V_{GS}=18\text{V}$			250	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=0.5\text{mA}$ $T_J=25^{\circ}\text{C}$ $T_J=175^{\circ}\text{C}$	2	2.9 2.0	4	V
$R_{DS(on)}$	Drain-Source On-State Resistance	$V_{GS}=18\text{V}$, $I_D=2\text{A}$ $T_J=25^{\circ}\text{C}$ $T_J=175^{\circ}\text{C}$		565 1010		m Ω

Dynamic Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{DS}=1000\text{V}$, $f=1\text{MHz}$, $V_{GS}=0\text{V}$		268		pF
C_{oss}	Output Capacitance			20.2		pF
C_{rss}	Reverse Transfer Capacitance			3.1		pF
$R_{G(int)}$	Internal Gate Resistance	$f=1\text{MHz}$		10.7		Ω
Q_g	Total Gate Charge	$V_{DS}=1200\text{V}$, $I_D=2\text{A}$, $V_{GS}=-4/18\text{V}$		20		nC
Q_{gs}	Gate to Source Charge			4		nC
Q_{gd}	Gate to Drain Charge			10		nC

Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(j-c)}$	Thermal Resistance from Junction to Case		1.53		$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

Switching Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=1200\text{V}$, $I_D=2\text{A}$, $V_{GS}=-4\text{V}/18\text{V}$, $R_{G(ext)}=2.5\Omega$, $L=600\mu\text{H}$		9		ns
t_r	Rise Time			16		ns
$t_{d(off)}$	Turn-Off Delay Time			11		ns
t_f	Fall Time			97		ns
E_{on}	Turn-On Energy			133		μJ
E_{off}	Turn-Off Energy			16		μJ

Reverse Diode Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V_{SD}	Diode Forward Voltage	$V_{GS}=-4\text{V}$, $I_{SD}=1\text{A}$ $T_J=25^{\circ}\text{C}$ $T_J=175^{\circ}\text{C}$ $V_{GS}=-4\text{V}$, $I_{SD}=2\text{A}$ $T_J=25^{\circ}\text{C}$ $T_J=175^{\circ}\text{C}$		4.0 3.5 4.6 3.9		V
I_S	Continuous Diode Forward Current	$V_{GS}=-4\text{V}$ $T_C=25^{\circ}\text{C}$ $T_C=100^{\circ}\text{C}$		9 6		A
t_{rr}	Reverse Recovery Time	$V_{GS}=-4\text{V}$, $I_{SD}=2\text{A}$, $V_R=1200\text{V}$, $di/dt=906\text{A}/\mu\text{s}$		60		ns
Q_{rr}	Reverse Recovery Charge			98		nC
I_{rrm}	Peak Reverse Recovery Current			2.8		A

RATING AND CHARACTERISTIC CURVES

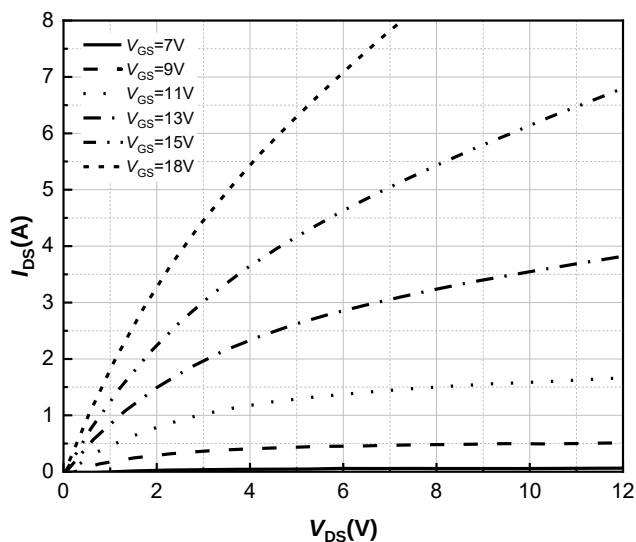


Figure 1. Output Characteristics
 $T_j = -40^\circ\text{C}$

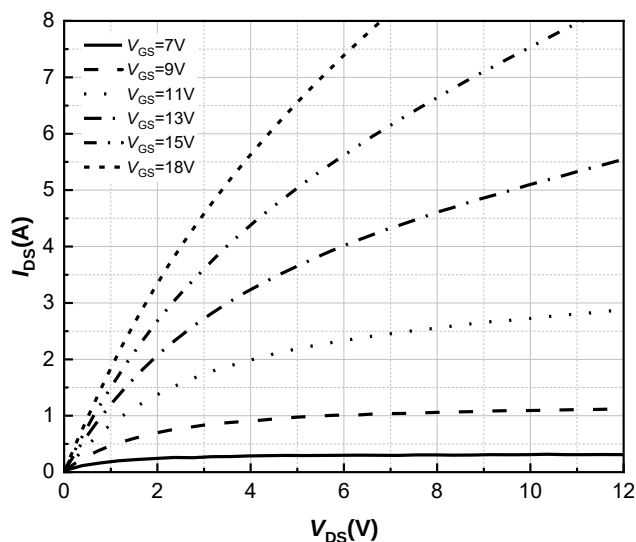


Figure 2. Output Characteristics
 $T_j = 25^\circ\text{C}$

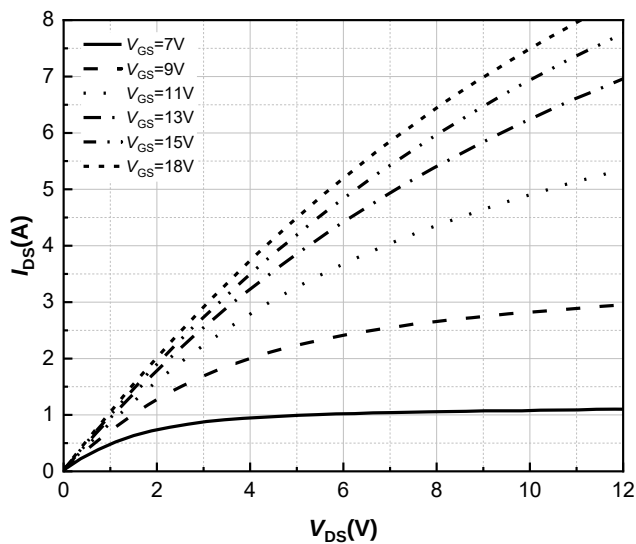


Figure 3. Output Characteristics
 $T_j = 175^\circ\text{C}$

Figure 3. Output Characteristics
 $T_j = 175^\circ\text{C}$

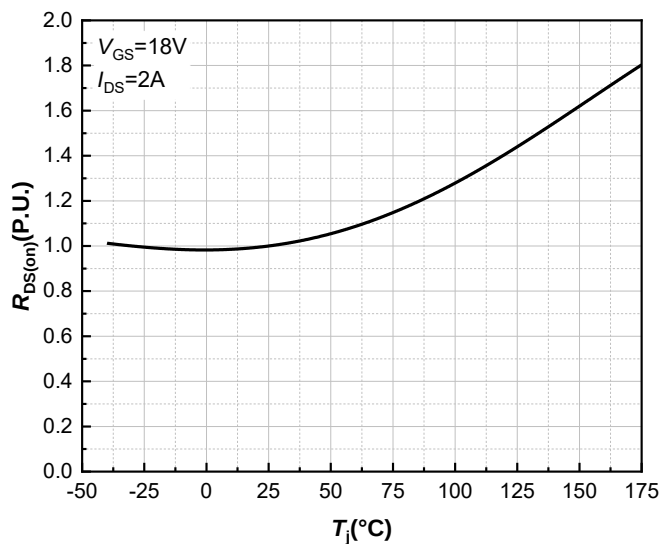


Figure 4. Normalized On-Resistance vs.
Temperature

Figure 4. Normalized On-Resistance vs.
Temperature

RATING AND CHARACTERISTIC CURVES

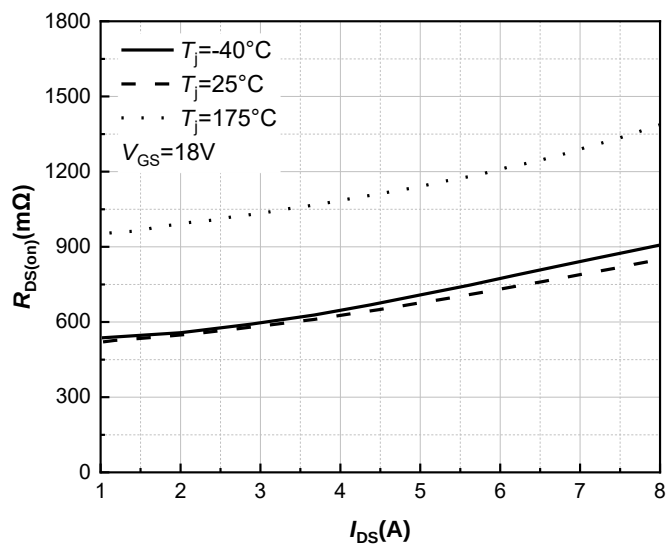


Figure 5. On-Resistance vs. Drain Current For Various Temperatures

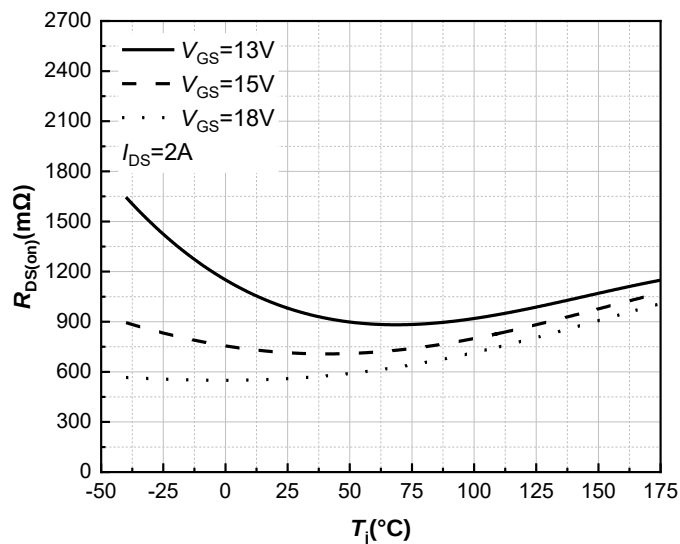


Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

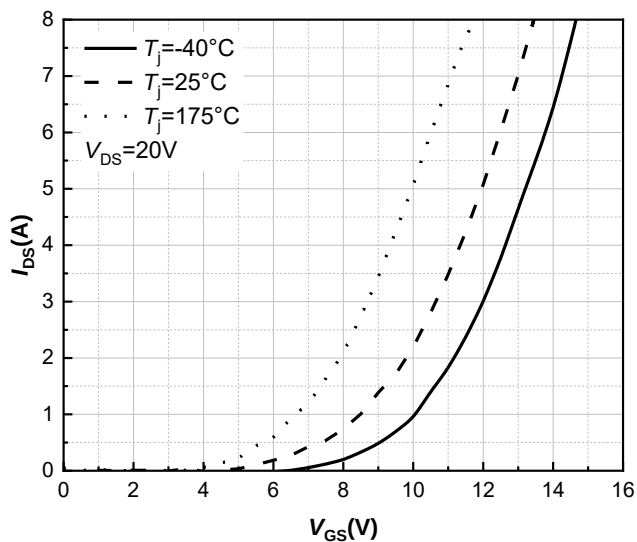


Figure 7. Transfer Characteristic for Various Junction Temperatures

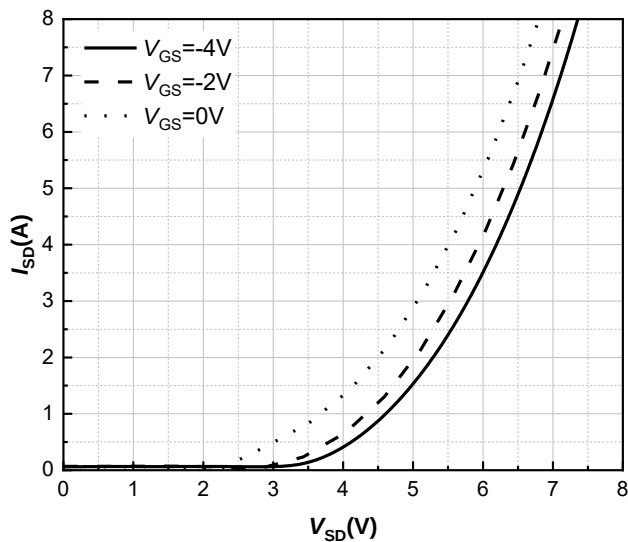


Figure 8. Body Diode Characteristic $T_J = -40^{\circ}\text{C}$

RATING AND CHARACTERISTIC CURVES

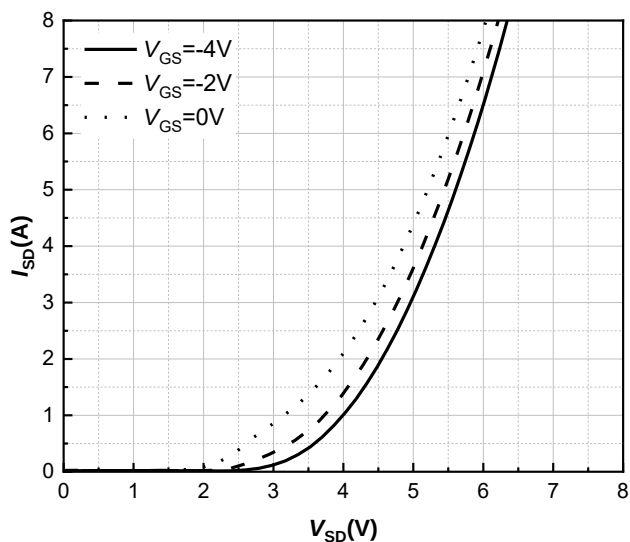


Figure 9. **Body Diode Characteristic**
 $T_j=25^{\circ}\text{C}$

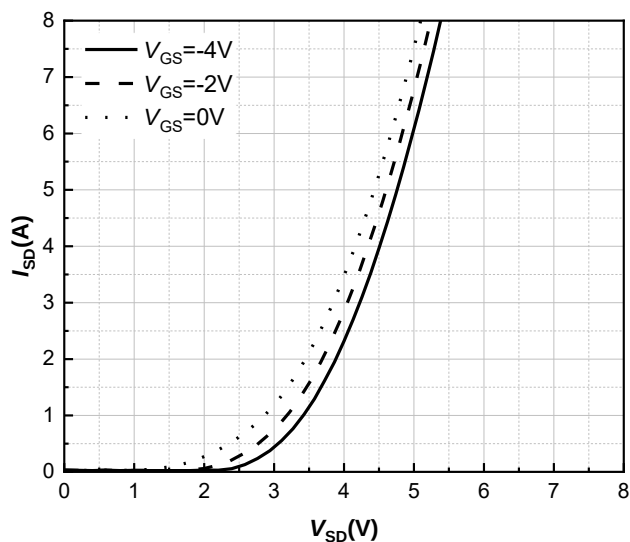


Figure 10. **Body Diode Characteristic**
 $T_j=175^{\circ}\text{C}$

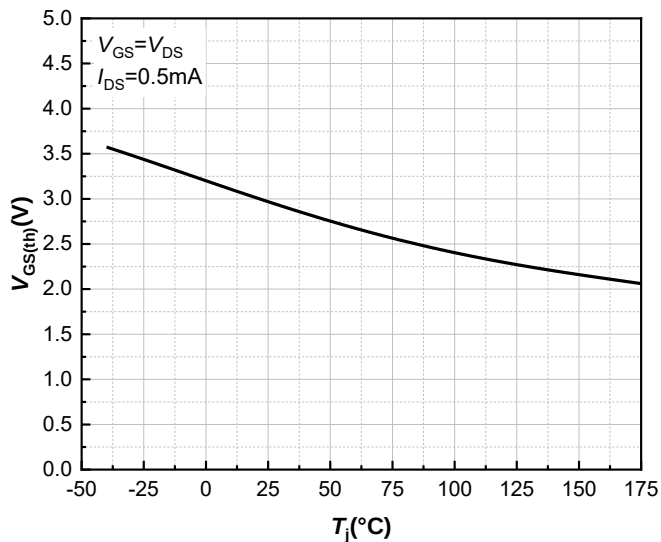


Figure 11. **Threshold Voltage vs. Temperature**

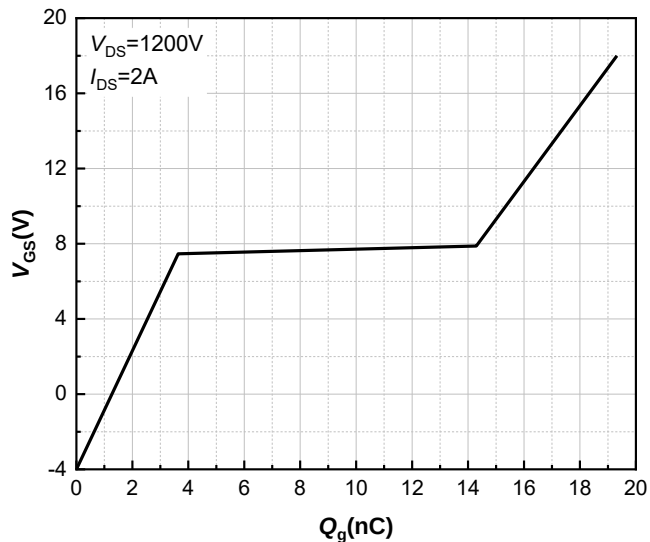


Figure 12. **Gate Charge Characteristics**

RATING AND CHARACTERISTIC CURVES

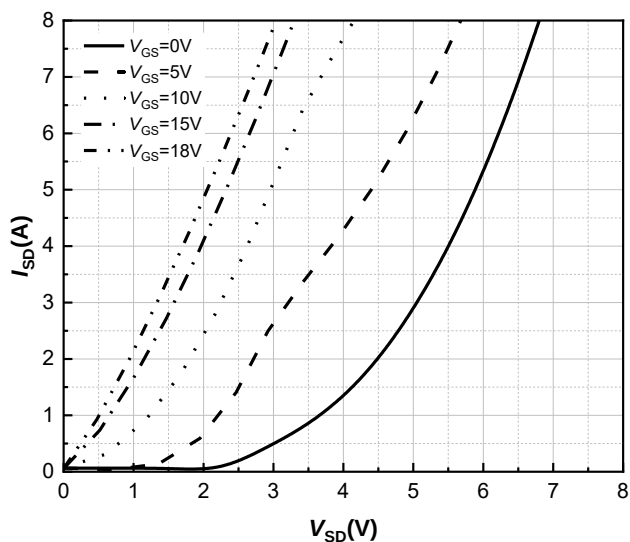


Figure 13. 3rd Quadrant Characteristic
 $T_j = -40^{\circ}\text{C}$

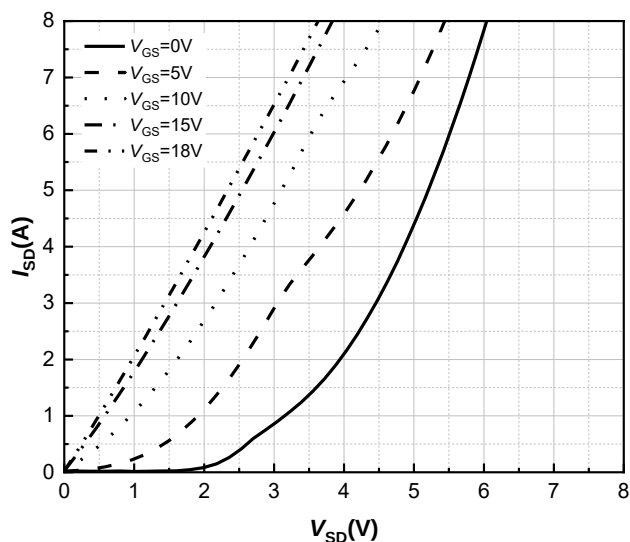


Figure 14. 3rd Quadrant Characteristic
 $T_j = 25^{\circ}\text{C}$

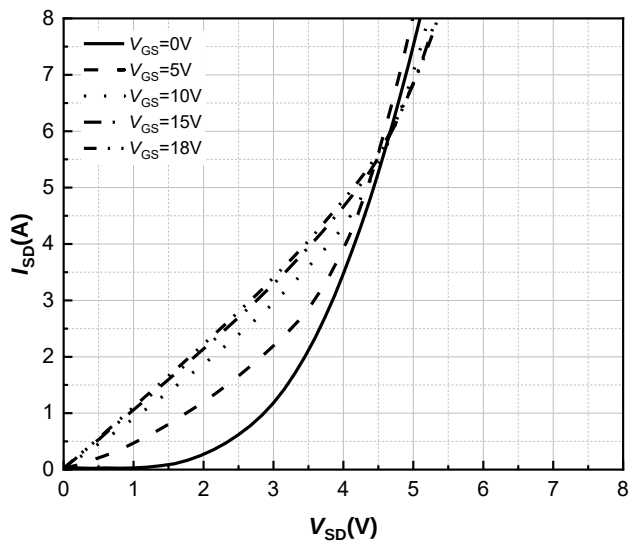


Figure 15. 3rd Quadrant Characteristic
 $T_j = 175^{\circ}\text{C}$

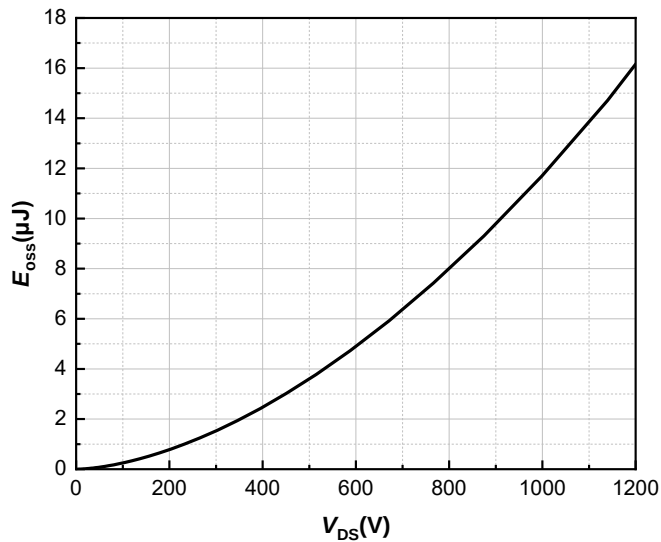


Figure 16. Output Capacitor Stored
Energy

RATING AND CHARACTERISTIC CURVES

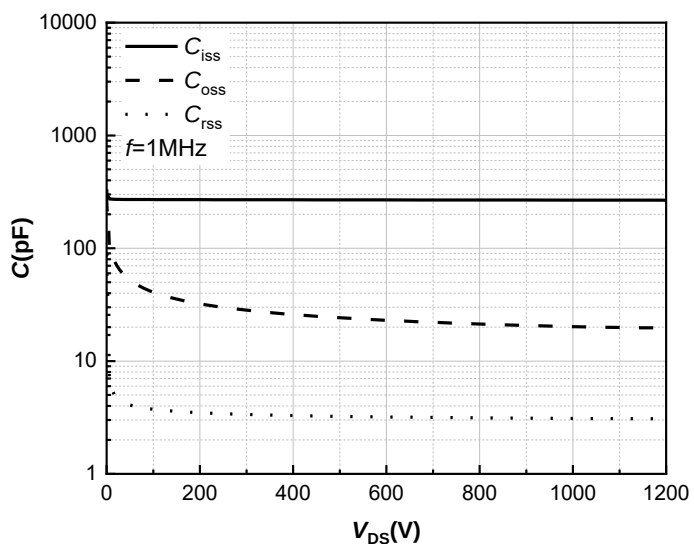


Figure 17. Capacitances vs. Drain-Source

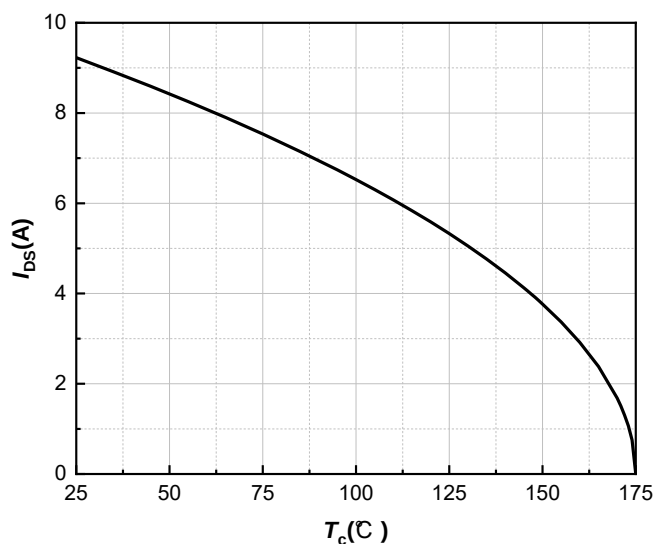


Figure 18. Continuous Drain Current Derating vs. Case Temperature

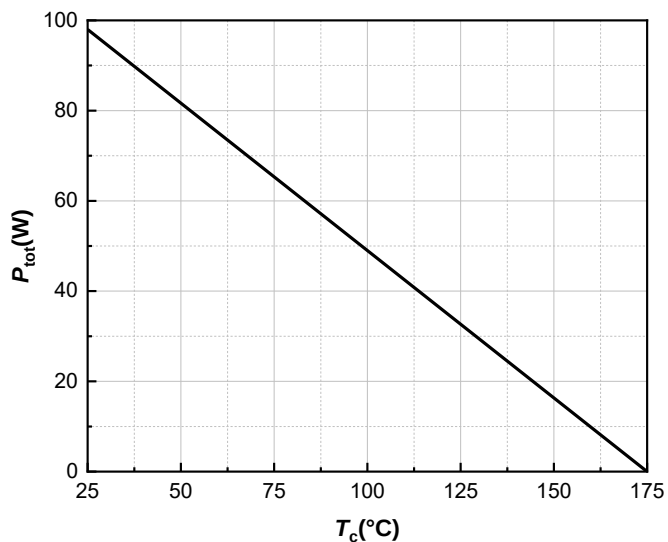


Figure 19. Maximum Power Dissipation Derating vs. Case Temperature

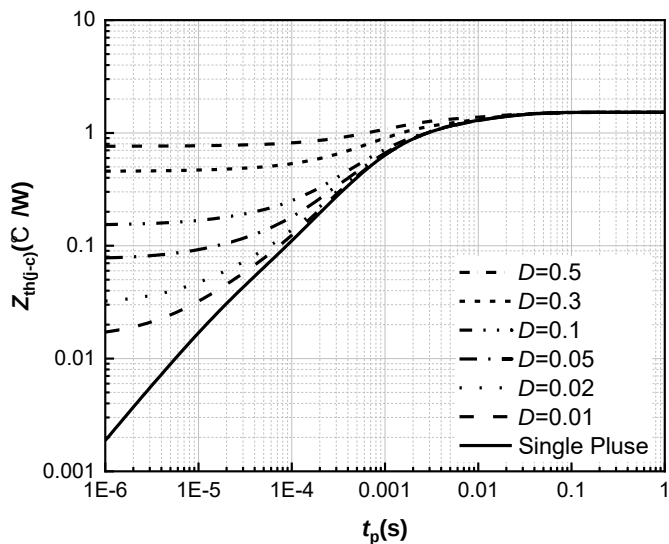


Figure 20. Transient Thermal Impedance

RATING AND CHARACTERISTIC CURVES

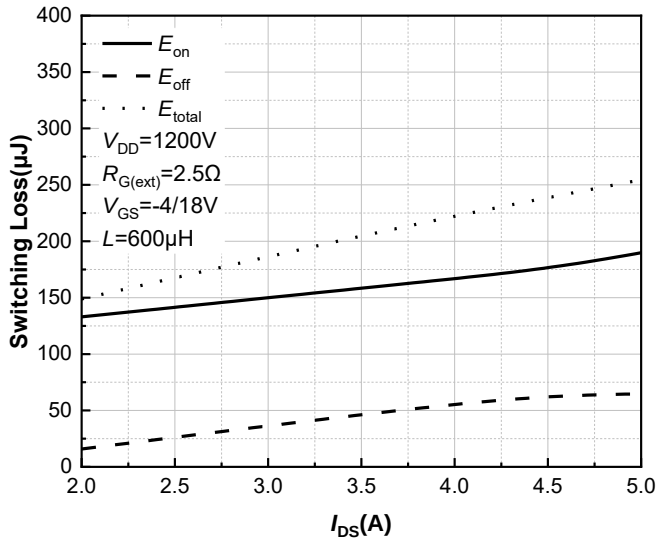


Figure 21. Clamped Inductive Switching Energy vs. Drain Current

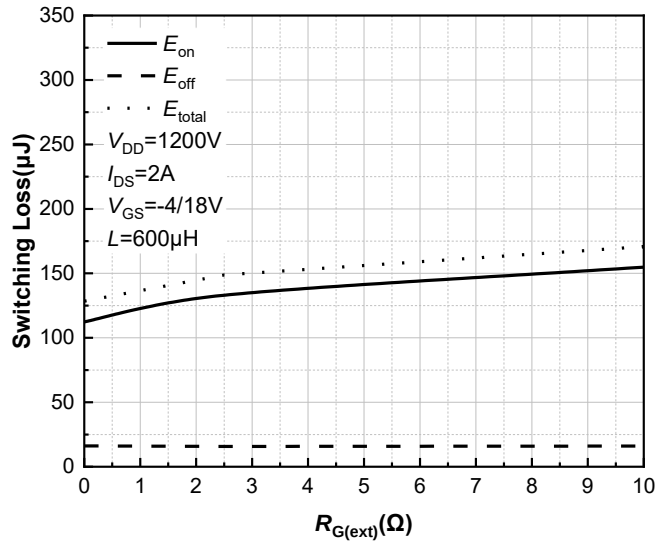


Figure 22. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

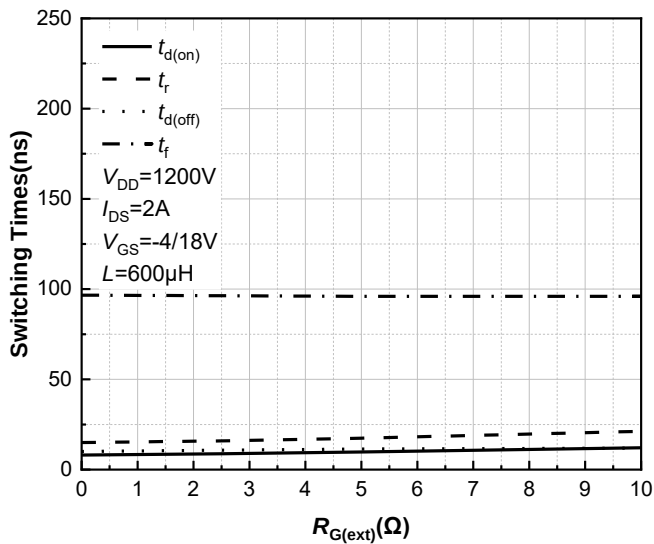


Figure 23. Switching Times vs. $R_{G(ext)}$

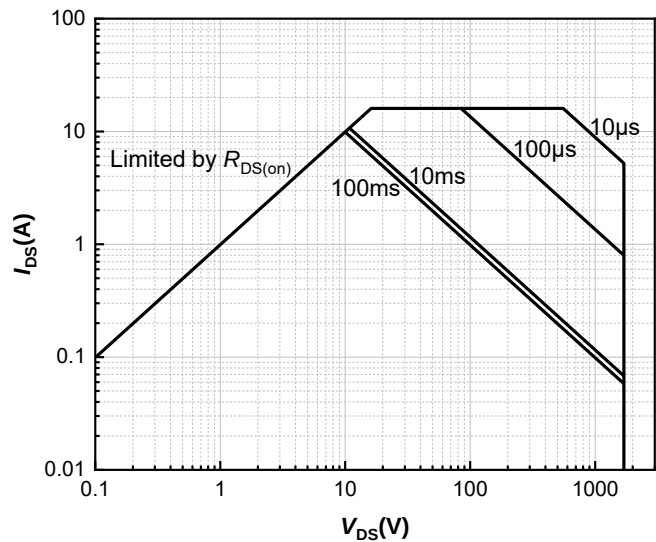
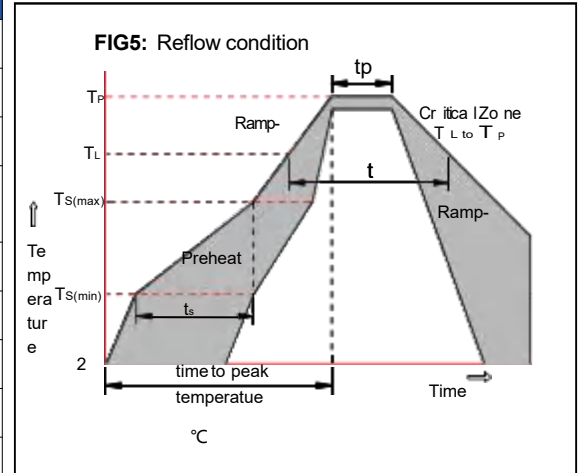


Figure 24. Safe Operating Area

Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217 °C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C



Package Dimensions & Suggested Pad Layout

